

# Giang Dang

## List of Publications by Year in descending order

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papers

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#	ARTICLE	IF	CITATIONS
1	Fabrication of Zn <sub>1-x</sub> Mg <sub>x</sub> O/Ag <sub>2</sub> O Heterojunction Diodes by Mist CVD at Atmospheric Pressure. Applied Surface Science, 2022, , 153465.	6.1	0
2	Optical Characterization of Gallium Oxide $\hat{1}\pm$ and $\hat{1}^2$ Polymorph Thin-Films Grown on c-Plane Sapphire. Journal of Electronic Materials, 2021, 50, 2990-2998.	2.2	9
3	The effect of HCl on the $\hat{1}\pm$ -Ga <sub>2</sub> O <sub>3</sub> thin films fabricated by third generation mist chemical vapor deposition. AIP Advances, 2021, 11, 045123.	1.3	7
4	Sub- $\hat{1}\mu\text{m}$ features patterned with laser interference lithography for the epitaxial lateral overgrowth of $\hat{1}\pm$ -Ga <sub>2</sub> O <sub>3</sub> via mist chemical vapor deposition. Applied Physics Letters, 2021, 119, 041902.	3.3	6
5	The Quality Improvement of Yttrium Oxide Thin Films Grown at Low Temperature via the Third-Generation Mist Chemical Vapor Deposition Using Oxygen-Supporting Sources. Physica Status Solidi (B): Basic Research, 2021, 258, 2100105.	1.5	5
6	$\hat{1}\pm$ -(Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> single-layer and heterostructure buffers for the growth of conductive Sn-doped $\hat{1}\pm$ -Ga <sub>2</sub> O <sub>3</sub> thin films via mist chemical vapor deposition. APL Materials, 2020, 8, .	5.1	15
7	Conductive Si-doped $\hat{1}\pm$ -(Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> thin films with the bandgaps up to 6.22 eV. AIP Advances, 2020, 10, 115019.	1.3	13
8	Electronic devices fabricated on mist-CVD-grown oxide semiconductors and their applications. Japanese Journal of Applied Physics, 2019, 58, 090606.	1.5	22
9	Growth mechanism of zinc oxide thin film by mist chemical vapor deposition via the modulation of [H <sub>2</sub> O]/[Zn] ratios. Applied Physics Express, 2019, 12, 065505.	2.4	10
10	Composition control of Zn <sub>1-x</sub> Mg <sub>x</sub> O thin films grown using mist chemical vapor deposition. Japanese Journal of Applied Physics, 2019, 58, 035503.	1.5	10
11	Challenges of fabrication of a large-area-uniform molybdenum disulfide layered thin film at low growth temperature by atmospheric-pressure solution-based mist CVD. Japanese Journal of Applied Physics, 2018, 57, 110306.	1.5	6
12	Growth of $\hat{1}\pm$ -Cr <sub>2</sub> O <sub>3</sub> single crystals by mist CVD using ammonium dichromate. Applied Physics Express, 2018, 11, 111101.	2.4	11
13	Bandgap engineering of $\hat{1}\pm$ -(Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> by a mist chemical vapor deposition two-chamber system and verification of Vegard's Law. Applied Physics Letters, 2018, 113, .	3.3	64
14	Zinc tin oxide metal semiconductor field effect transistors and their improvement under negative bias (illumination) temperature stress. Applied Physics Letters, 2017, 110, 073502.	3.3	22
15	Incorporation of yttrium to yttrium iron garnet thin films fabricated by mist CVD. Japanese Journal of Applied Physics, 2017, 56, 04CJ02.	1.5	2
16	Silver oxide Schottky contacts and metal semiconductor field-effect transistors on SnO <sub>2</sub> thin films. Applied Physics Express, 2016, 9, 041101.	2.4	30
17	Atmospheric-pressure epitaxial growth technique of a multiple quantum well by mist chemical vapor deposition based on Leidenfrost droplets. Applied Physics Letters, 2016, 109, .	3.3	16
18	Stability of In-Ga-Zn-O metal-semiconductor field-effect-transistors under bias, illumination, and temperature stress. Applied Physics Letters, 2015, 107, .	3.3	16

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19	Metal-Semiconductor Field-Effect Transistors With In <sub>0.2</sub> Ga <sub>0.8</sub> ZnO Channel Grown by Nonvacuum-Processed Mist Chemical Vapor Deposition. IEEE Electron Device Letters, 2015, 36, 463-465.	3.9	37
20	Mist-CVD Grown Sn-Doped $\alpha$ -Ga <sub>2</sub> O <sub>3</sub> MESFETs. IEEE Transactions on Electron Devices, 2015, 62, 3640-3644.	3.0	97
21	Characterization of Tin Oxide Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2014, 1633, 13-18.	0.1	1
22	Reflectance, transmittance, and absorbance of ZnO implanted with 60keV Sn <sup>+</sup> ions. Surface and Coatings Technology, 2013, 229, 125-129.	4.8	0
23	Successful Growth of Conductive Highly Crystalline Sn-Doped $\alpha$ -Ga <sub>2</sub> O <sub>3</sub> Thin Films by Fine-Channel Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 040207.	1.5	113
24	Successful Growth of Conductive Highly Crystalline Sn-Doped $\alpha$ -Ga <sub>2</sub> O <sub>3</sub> Thin Films by Fine-Channel Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 040207.	1.5	20
25	Photoluminescence, morphology, and structure of hydrothermal ZnO implanted at room temperature with 60 keV Sn <sup>+</sup> ions. Journal of Applied Physics, 2011, 109, 123516.	2.5	3
26	Characteristics of ZnO Wafers Implanted with 60 keV Sn <sup>+</sup> Ions at Room Temperature and at 110 K. AIP Conference Proceedings, 2011, , .	0.4	1
27	Pulsed laser excitation power dependence of photoluminescence peak energies in bulk ZnO. Journal of Applied Physics, 2011, 110, 083508.	2.5	5
28	Photoluminescence of an Al <sub>0.5</sub> Ga <sub>0.5</sub> As/GaAs multiple quantum well in the temperature range from 5 to 400 K. Journal of Applied Physics, 2009, 106, .	2.5	11
29	Nonlinear absorption and refraction of CdSe/ZnS quantum dots at two-photon resonant excitation of excitons. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2507-2510.	0.8	4